

N-Channel Enhancement Mode Power MOSFET

Description

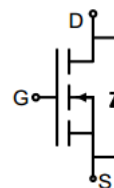
The GT100N12K uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

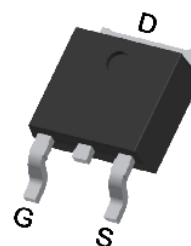
- V_{DS} 120V
- I_D (at $V_{GS} = 10V$) 70A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) $< 10m\Omega$
- 100% Avalanche Tested
- RoHS Compliant

Application

- Synchronous Rectification in SMPS or LED Driver
- UPS
- Motor Control
- BMS
- High Frequency Circuit



Schematic Diagram



TO-252

Device	Package	Marking	Packaging
GT100N12K	TO-252	GT100N12	2500pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	120	V
Continuous Drain Current	I_D	70	A
Pulsed Drain Current (note1)	I_{DM}	280	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	120	W
Single pulse avalanche energy (note3)	E_{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

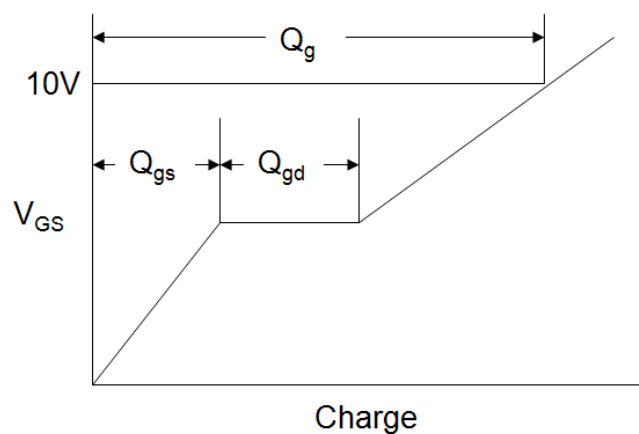
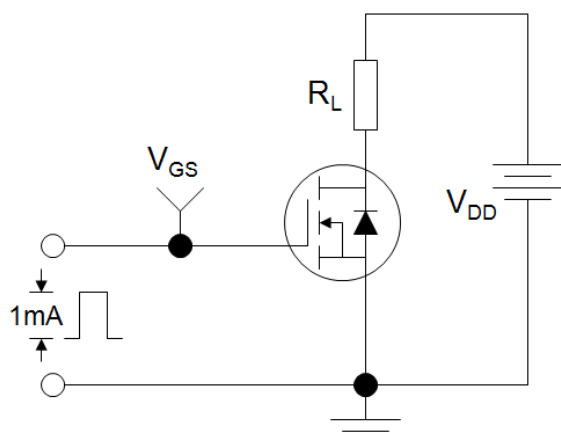
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.25	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	120	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.5	3	3.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 35A	--	9.2	12	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _b =35A	--	60	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 60V, f = 1.0MHz	--	3050	--	pF
Output Capacitance	C _{oss}		--	280	--	
Reverse Transfer Capacitance	C _{rss}		--	22	--	
Total Gate Charge	Q _g	V _{DS} = 60V, I _D = 35A, V _{GS} = 10V	--	50	--	nC
Gate-Source Charge	Q _{gs}		--	17	--	
Gate-Drain Charge	Q _{gd}		--	15	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 60V, I _D = 35A, R _G = 1.6Ω	--	15	--	ns
Turn-on Rise Time	t _r		--	10	--	
Turn-off Delay Time	t _{d(off)}		--	34	--	
Turn-off Fall Time	t _f		--	8	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	70	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 25A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	trr	I _S = 35A, V _{GS} = 0V di/dt=100A/us	--	60	--	ns

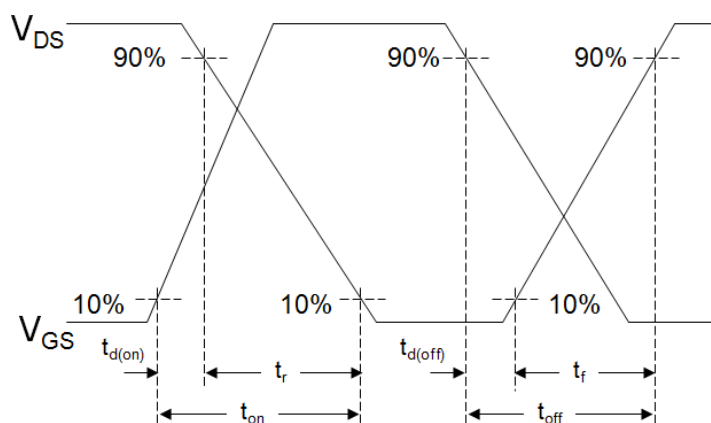
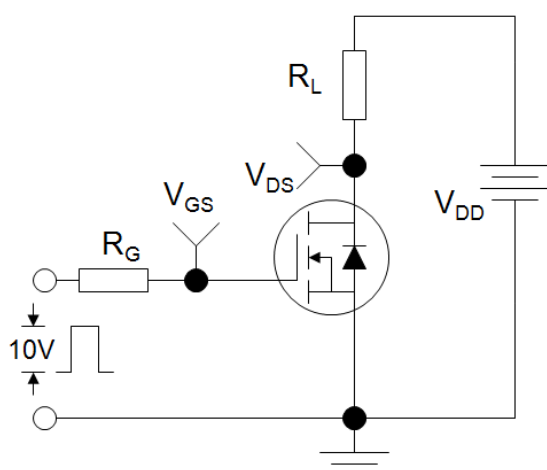
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : $T_J=25^\circ\text{C}$, $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25\Omega$

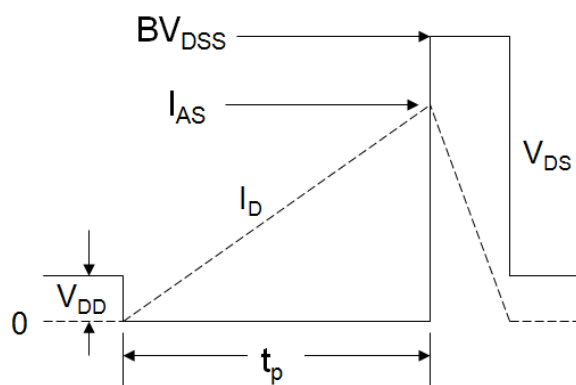
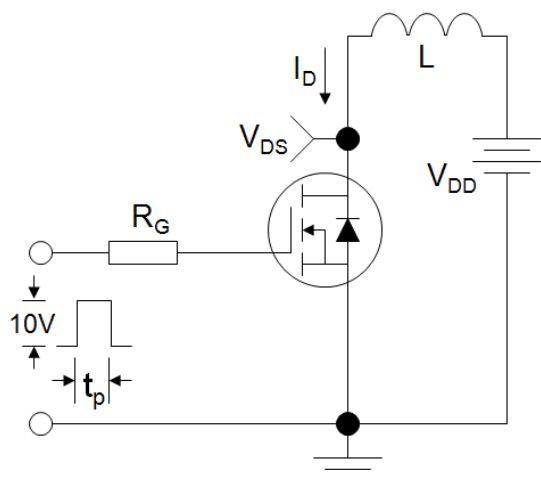
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

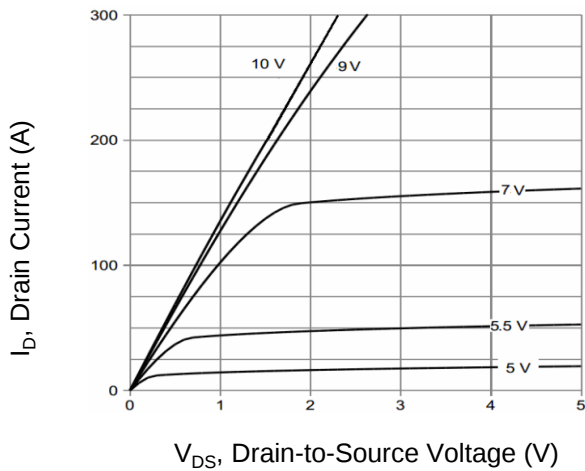


Figure 2. Transfer Characteristics

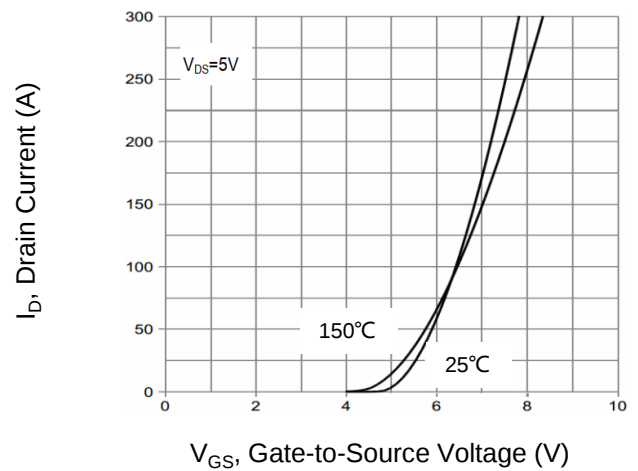


Figure 3. Gate Charge

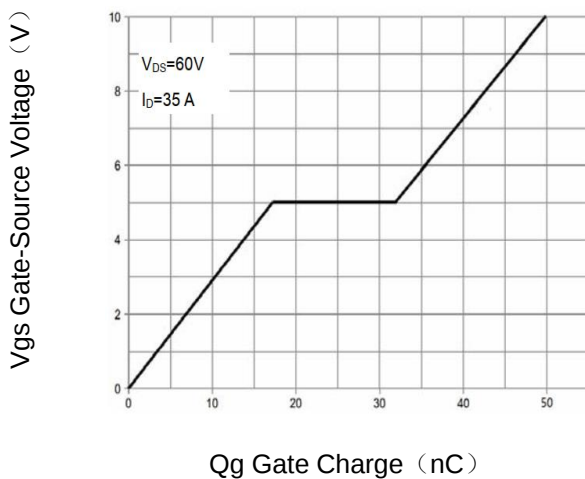


Figure 4. Drain Source On Resistance

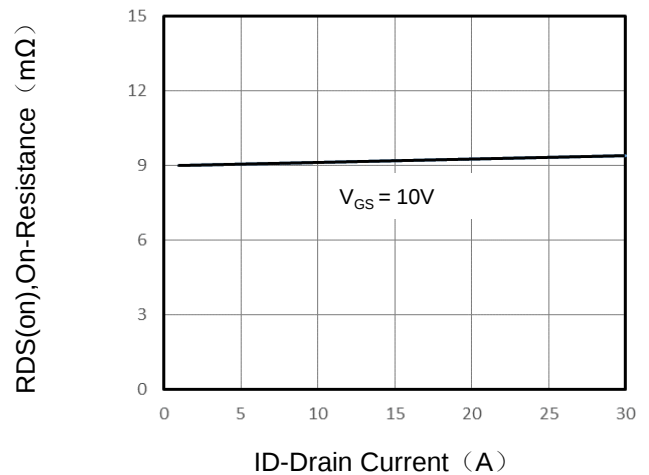


Figure 5. Capacitance vs Vds

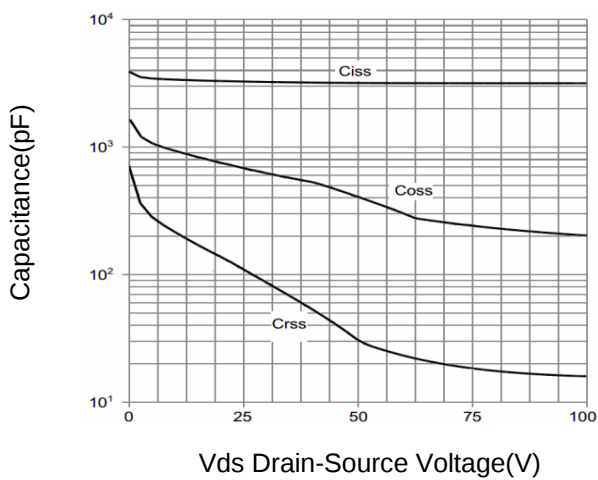
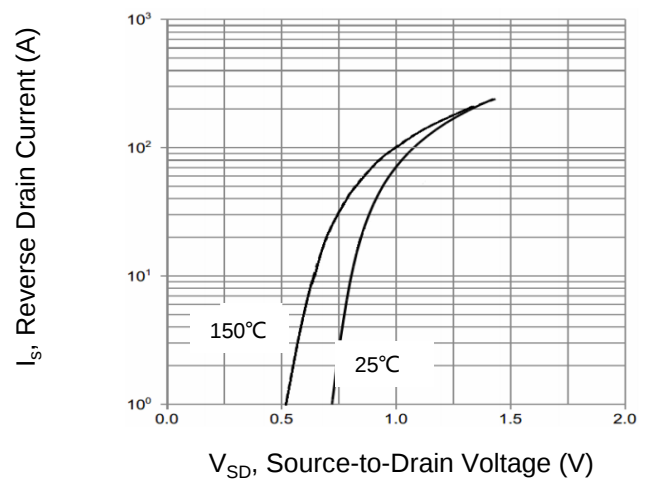


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

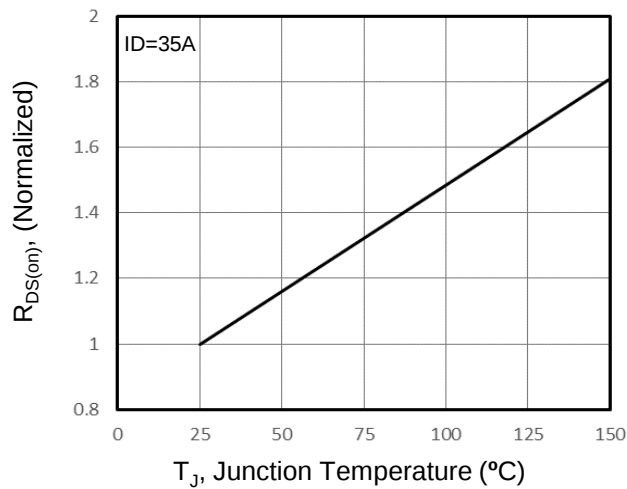


Figure 8. Safe Operation Area

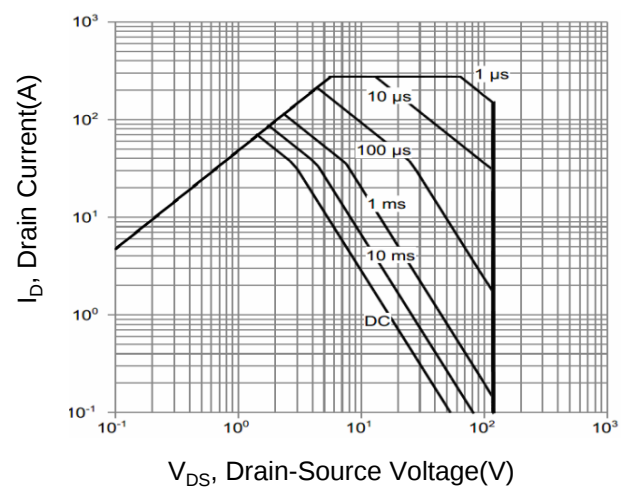
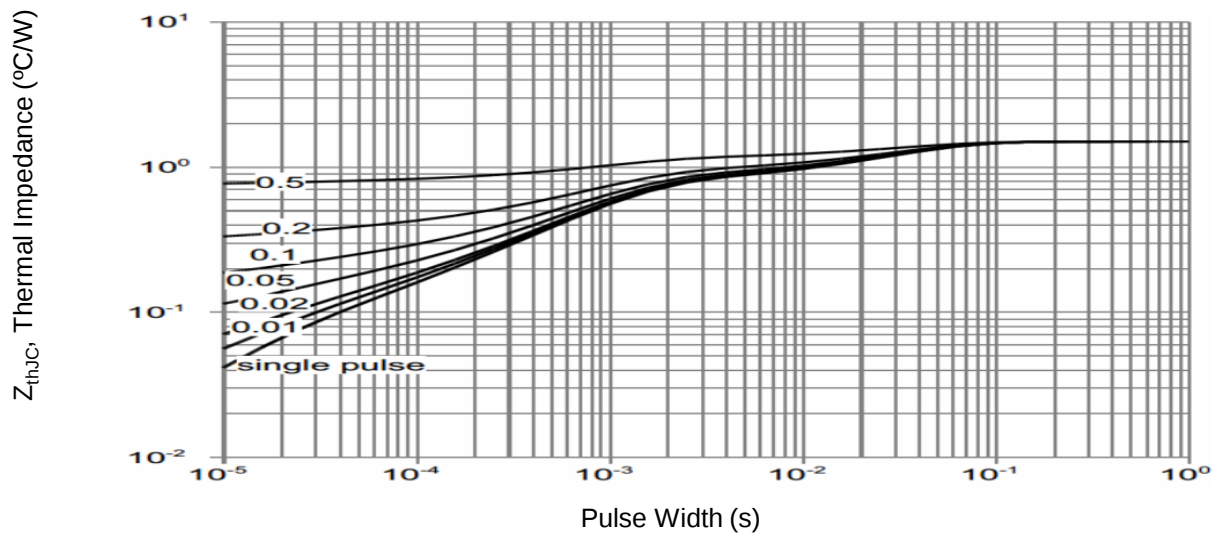
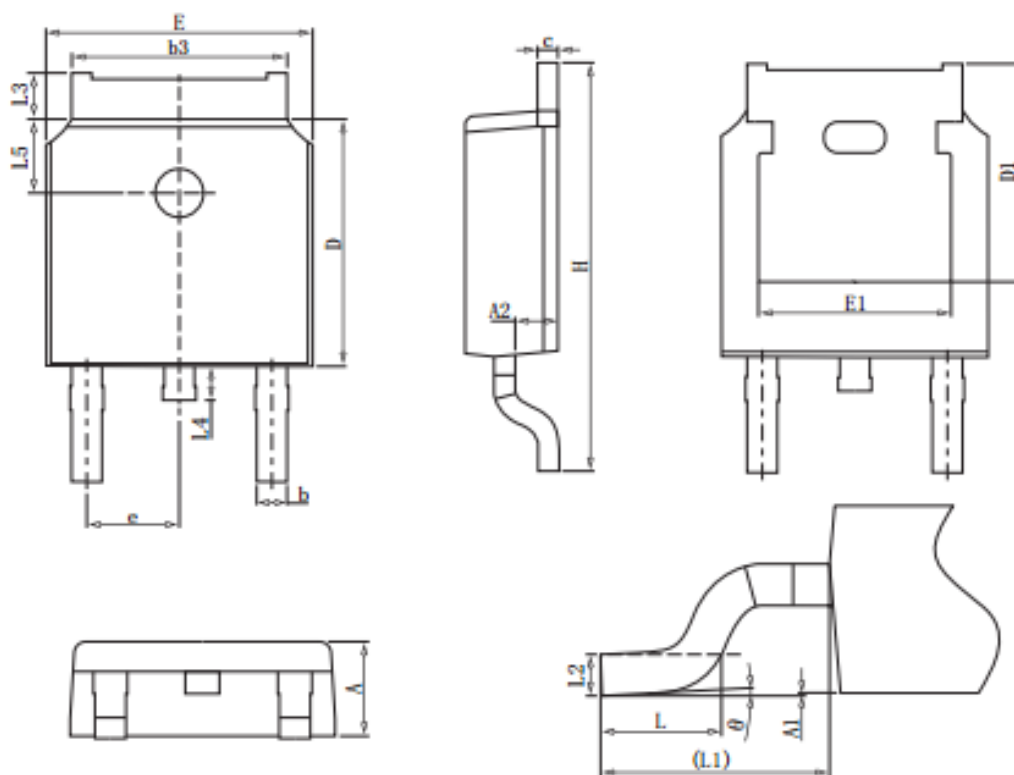


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.2	2.3	2.4
A1	0		0.2
A2	0.97	1.07	1.17
b	0.68	0.78	0.9
b3	5.2	5.33	5.5
c	0.43	0.53	0.63
D	5.98	6.1	6.22
D1	5.30REF		
E	6.4	6.6	6.8
E1	4.63		
e	2.286BSC		
H	9.4	10.1	10.5
L	1.38	1.5	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88		1.28
L4	0.5		1
L5	1.65	1.8	1.95
θ	0°		8°